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cancel*

a capacitor formed on the first insulating film, the capacitor having a dielectric film formed of either ferroelectric material or high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween; and

a silicon oxide film placed over the capacitor forming a planarized surface;

wherein nitrogen being introduced all over the planarized surface of the silicon oxide film.

5. (Amended) A semiconductor device comprising;

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B2*

a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;

a first insulating film for covering the transistor;

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a capacitor formed on the first insulating film, the capacitor having a dielectric formed of either ferroelectric material or high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;

a second insulating film formed on the capacitor;

a local interconnection formed on the second insulating film, for electrically connecting the upper electrode of the capacitor to the first impurity region;

a third insulating film formed on the local interconnection and the second insulating film;

a first wiring formed on the third insulating film and electrically connected to the second impurity region via a hole which is formed on the first insulating film, the second insulating film, and the third insulating film;

a fourth insulating film placed on the first wiring forming an upper planarized surface,

*A2
Concl'd.* wherein nitrogen being introduced all over the upper planarized surface of the fourth insulating film; and
a second wiring formed on the fourth insulating film.

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B3* 12. (Amended) a semiconductor device comprising:

a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;

A3 a first insulating film for covering the transistor;

a capacitor formed on the first insulating film, the capacitor having a dielectric film formed of either ferroelectric material or high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;

a second insulating film covering the capacitor to become an upper planarized surface; and

wherein a surface of the second insulating film is planarized and nitrogen is introduced by plasma processing all over the upper planarized surface of the second insulating film.
